

Silicon PNP Power Transistors

2SA1184

DESCRIPTION

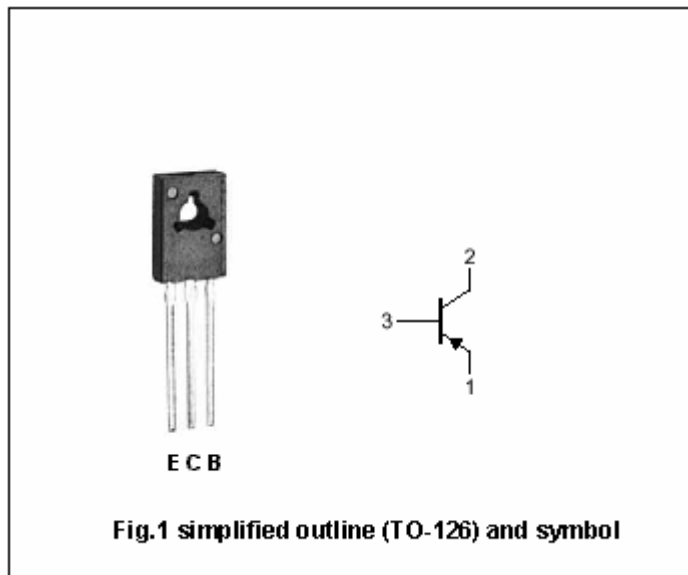
- With TO-126 package
- High breakdown voltage

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1	A
I_B	Base current		-0.1	A
P_D	Total power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_C=25^\circ\text{C}$	15	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55 $^\circ\text{C}$ +150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-120			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10μA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-500mA ; V _{CE} =-5V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1	μA
h _{FE}	DC current gain	I _C =-100mA ; V _{CE} =-5V	80		240	
f _T	Transition frequency	I _C =-0.1A ; V _{CE} =5V		120		MHz

PACKAGE OUTLINE

